## ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Flectronic Version v18 Stylesheet Version v18.0

> Title of Invention

METHOD OF FABRICATING A CMOS DEVICE WITH DUAL METAL GATE ELECTRODES

Application Number :

10/826665

Confirmation Number: First Named Applicant: CHANG PARK

9608

Attorney Docket Number: 61472-0308425

Art Unit:

Examiner:

Search string:

( 6653698 or 6352913 ).pn

## **US Patent Documents**

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6653698	2003-11-25	LEE ET AL.	B2	257	407
	2	6352913	2002-03-05	MISTRY ET AL.	B1	438	587

## Signature

Examiner Name	Date		